MGBR20L200C DIODE

DUAL MOS GATED BARRIER RECTIFIER

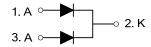
■ DESCRIPTION

The UTC MGBR20L200C is a dual mos gated barrier rectifiers,it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

■ FEATURES

- * Low forward voltage drop
- * High switching speed

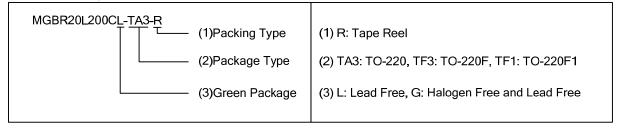
■ SYMBOL



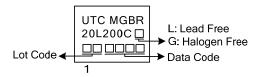
ORDERING INFORMATION

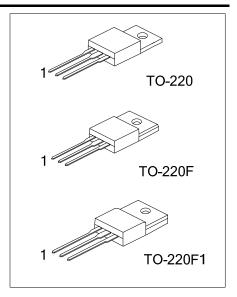
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20L200CL-TA3-T	MGBR20L200CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR20L200CL-TF3-T	MGBR20L200CG-TF3-T	TO-220F	Α	K	Α	Tube	
MGBR20L200CL-TF1-T	MGBR20L200CG-TF1-T	TO-220F1	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Common Cathode



MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	200	V
WorkingPeak Reverse Voltage		V_{RWM}	200	V
Peak Repetitive Reverse Voltage		V_{RRM}	200	V
Average Rectified Output Current	Per Leg	1	10	Α
(T _C =140°C)	Total	l _O	20	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	180	А
Repetitive Peak Avalanche Power (1µs, 25°C)		P _{ARM}	5000	W
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL RESISTANCES CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient		θ_{JA}	62.5	°C/W	
Junction to Case	TO-220	0	2	°C/W	
	TO-220F/TO-220F1	$\theta_{ m JC}$	3.31	C/VV	

■ ELECTRICAL CHARACTERISTICS(Per Leg) (T_A=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA	200			V
Instantaneous Forward Voltage Drop	VEM	I _F =10A, T _J =25°C			0.86	V
		I _F =10A, T _J =125°C			0.78	V
Leakage Current (Note 1)	lъм	V _R =200V, T _J =25°C			100	μA
		V _R =200V, T _J =125°C			10	mΑ

Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

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